

Depletion-Mode Power MOSFET

General Features

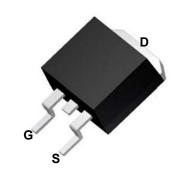
- ➤ Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- ➤ RoHS Compliant
- > Halogen-free available

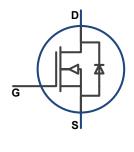
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- Suppressing surge current
- Normally-on Switches
- Converters
- > Synchronous Rectification
- Linear Amplifier
- Constant Current Source
- Protection Circuits

BV _{DSX}	RDS(ON) (Max.)	I_D
200V	100mΩ	16A

TO-263





Ordering Information

Part Number	Package	Marking	Remark	
DMB2014	DMB2014 TO-263		Halogen Free	

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

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Symbol	Parameter	DMB2014	Unit			
$V_{ m DSX}$	Drain-to-Source Voltage ^[1]	200	V			
V _{DGX}	Drain-to-Gate Voltage ^[1]	200	V			
I_D	Continuous Drain Current	16				
I_{DM}	Pulsed Drain Current ^[2]	64	A			
D	Power Dissipation	230	W			
P_{D}	Derating Factor above 25℃	1.85	W/°C			
V_{GS}	Gate-to-Source Voltage	±20	V			
$T_{ m L}$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^{\circ}$			
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150				

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMB2014	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.54	K/W



Electrical Characteristics

OFF Characteristics

 $T_A = 25$ °C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	200	1		V	V_{GS} =-5V, I_D =250 μA
			1	1	μΑ	$V_{DS}=200V$, $V_{GS}=-5V$
$I_{D(OFF)}$	Drain-to-Source Leakage Current		1	1	mA	V_{DS} =200V, V_{GS} =-5V T_J =125°C
I_{GSS}	Gate-to-Source Leakage Current		1	1	η Λ	$V_{GS} = +20V, V_{DS} = 0V$
			1	-1	uA	V_{GS} =-20V, V_{DS} =0V

ON Characteristics

$T_A = 25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
I _{DSS}	Saturated Drain-to-Source Current	16			A	$V_{GS}=0V, V_{DS}=25V^{[3]}$
R _{DS(ON)}	Static Drain-to-Source On-Resistance		80	100	mΩ	$V_{GS}=0V$, $I_D=8A^{[3]}$
			65	90	mΩ	V _{GS} =5V, I _D =8A ^[3]
V _{GS(OFF)}	Gate-to-Source Cut-off Voltage	-3.3		-1.5	V	$V_{DS} = 3V, I_D = 8\mu A$
gfs	Forward Transconductance		6.1		S	$V_{DS} = 20V, I_D = 8A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance					V _{GS} =-5V
Coss	Oput Capacitance				pF	$V_{DS}=25V$
C _{RSS}	Reverse Transfer Capacitance					$f=1.0MH_Z$
Q _G	Total Gate Charge					
Q _{GS}	Gate-to-Source Charge				nC	V_{GS} =-5V~5V V_{DS} =100V, I_{D} =8A
Q _{GD}	Gate-to-Drain (Miller) Charge					

Resistive Switching Characteristics

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Essenfially	independent	t of operating	temperature
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Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
t _{d(ON)}	Turn-on Delay Time					
t _{rise}	Rise Time				40.0	$V_{GS} = -5V \sim 5V$
t _{d(OFF)}	Turn-off Delay Time				ns	$V_{DD} = 100 \text{V}, I_D = 8 \text{A}$ $R_G = 20 \text{Ohm}$
t_{fall}	Fall Time					_



Source-Drain Diode Characteristics

 $T_A=25$ °C unless otherwise specified

Symbol	Parameter	Min	Тур.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage		1	1.5	V	$I_{SD} = 8.0 \text{ A}, V_{GS} = -10 \text{ V}$

NOTE:

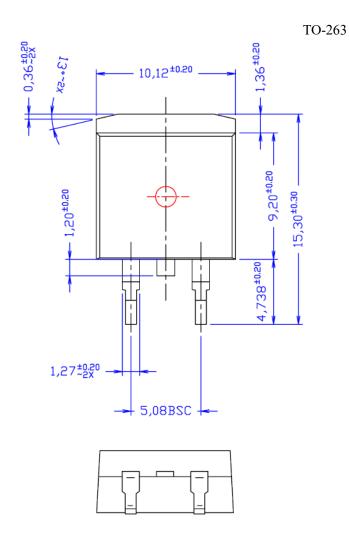
^[1] $T_J = +25^{\circ}C$ to $+150^{\circ}C$

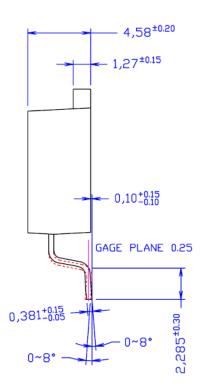
^[2] Repetitive rating, pulse width limited by maximum junction temperature.

^[3] Pulse width \(\le 380\mu s; \) duty cycle \(\le 2\%.



Package Dimensions







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